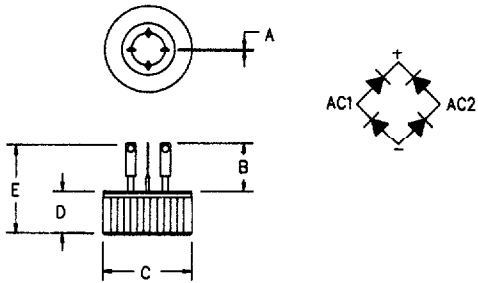


Single Phase Bridge Modules MT200 — MT800



Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	.020	.030	.508	.762	
B	.350	.370	8.89	9.40	
C	.745	.760	18.92	19.30	Dia.
D	.405	.420	10.29	10.67	
E	.775	.795	19.68	20.19	



Microsemi Catalog Number	Repetitive Peak Reverse Voltage
MT200*	200V
MT400*	400V
MT600*	600V
MT800*	800V

*Available with T03 mounting flange
For other circuit configurations, consult factory

- Glass Passivated Die
- Glass to metal construction
- Single phase rectification
- Available to 800 Volts
- Cup electrically isolated from terminals

Electrical Characteristics		
Maximum DC output current, single phase	I_D 25 Amps	Sine wave, 180° conduction
Maximum case temperature	T_C 137°C	
Maximum surge current per diode	I_{FSM} 250 Amps	8.3ms, half sine, $T_J = 175^\circ\text{C}$
Max i^2t for fusing	i^2t 260 A^2s	
Max peak forward voltage per diode	V _{FM} 1.2 Volts	@ I_o ; $T_J = 25^\circ\text{C}$ *
Max peak reverse current per diode	I_{RM} 1.0 mA	$V_{RRM, T_J} = 150^\circ\text{C}$
Minimum isolation voltage	V_{ISOL} 2500 VRMS	any terminal to case

*Pulse test: Pulse width 300 μsec , Duty cycle 2%

Thermal and Mechanical Characteristics		
Storage temperature range	T_{STG}	-65°C to 200°C
Operating junction temperature range	T_J	-65°C to 200°C
Maximum thermal resistance per diode	$R_{\theta JC}$	2.0°C/W Junction to Lead
Typical thermal resistance	$R_{\theta CS}$	0.2°C/W Case to sink
Weight		0.53 ounces (15.0 grams) typical

PH: 303-469-2161
FAX: 303-466-3775

Microsemi Corp.
6 Colorado

E-65

MT200 — MT800

Figure 1
Typical Forward Characteristics — Per Diode

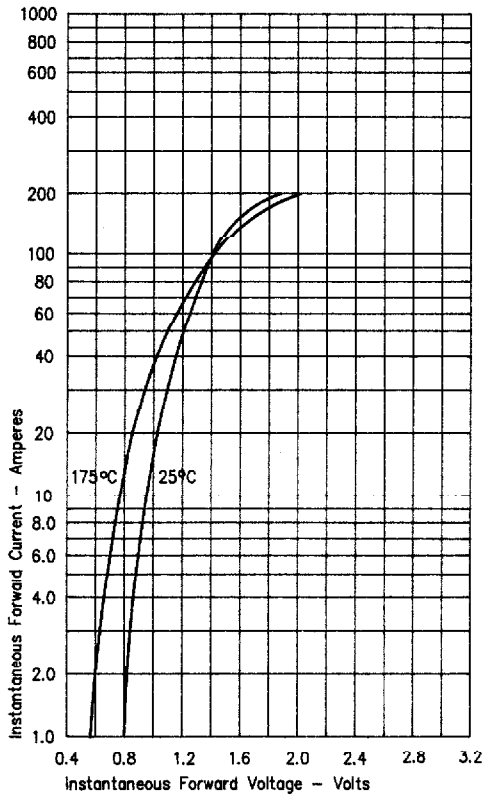


Figure 3
Maximum Nonrepetitive Surge Current — Per Diode

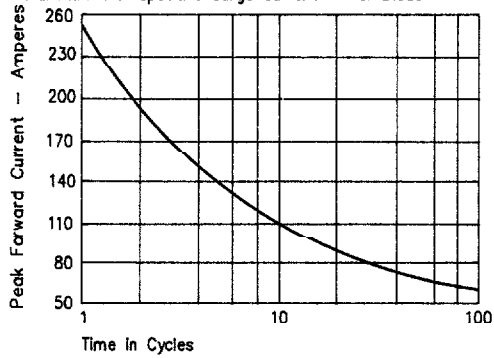


Figure 2
Forward Current Derating — Per Diode

